

Q10  
end

later. Thus, the shallow diffusion for the link base layer and the base can be achieved. A side wall forming SiO<sub>2</sub> film having a thickness of from 400 to 600 nm is formed over the surface. After that, the SiO<sub>2</sub> film is removed by anisotropic etching such as RIE so as to form side walls 7a made of the SiO<sub>2</sub> film. The side wall 7a has a function of isolating the base electrode from an emitter electrode which will be formed later. --

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Please replace the paragraph beginning at page 18, line 19, with the following rewritten paragraph:

an

--As shown in the figure, the diffusion depth of the link base layer 11 is equal to or less than that of the emitter 9, and the concentration of the link base layer 11 is equal to or more than that of the base 12. --

IN THE ABSTRACT:

Please replace the Abstract with the following:

Q12  
Contd

A bipolar transistor has a high performance and high reliability, which are obtained by enhancing a withstanding voltage between an emitter and a base. The bipolar transistor includes a first impurity diffusion layer in a semiconducting substrate, an opening disposed in the first conductive film. A third impurity diffusion